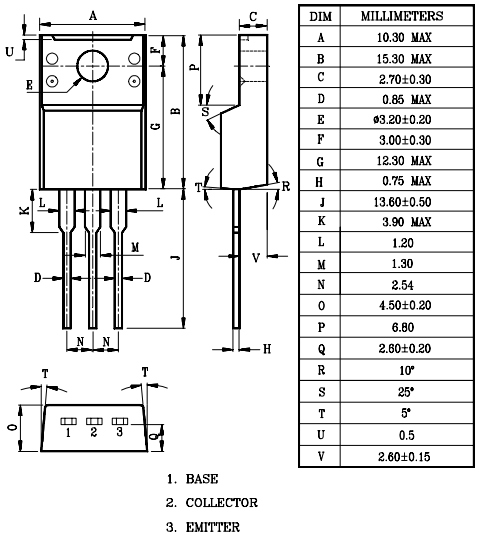
KTB1366

TRIPLE DIFFUSED PNP TRANSISTOR

GENERAL PURPOSE APPLICATION.

FEATURES

- Low Collector Saturation Voltage
  : $V_{CE(sat)}$=-1.0V(Max.) at I_C=-2A, I_B=-0.2A.
- Collector Power Dissipation
  : P_C=25W (Tc=25℃)
- Complementary to KTD2058.



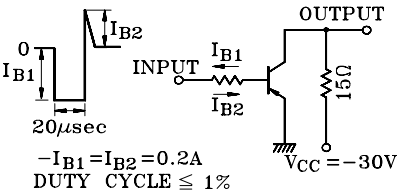
DIM	MILLIMETERS
A	10.30 MAX
B	15.30 MAX
C	2.70±0.30
D	0.85 MAX
E	ø3.20±0.20
F	3.00±0.30
G	12.30 MAX
H	0.75 MAX
J	13.60±0.50
K	3.90 MAX
L	1.20
M	1.30
N	2.54
O	4.50±0.20
P	6.80
Q	2.60±0.20
R	10°
S	25°
T	5°
U	0.5
V	2.60±0.15

TO-220IS

MAXIMUM RATINGS (Ta=25℃)

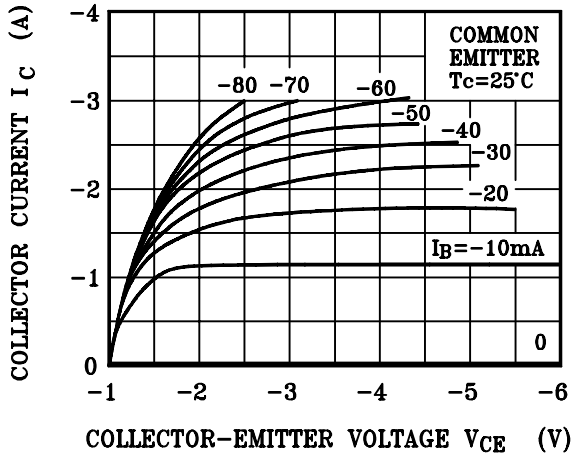
CHARACTERISTIC		SYMBOL	RATING	UNIT
Collector-Base Voltage		V_{CBO}	-60	V
Collector-Emitter Voltage		V_{CEO}	-60	V
Emitter-Base Voltage		V_{EBO}	-7	V
Collector Current		I_C	-3	A
Base Current		I_B	-0.5	A
Collector Power Dissipation	Ta=25℃	P_C	2	W
	Tc=25℃		25	
Junction Temperature		T_j	150	℃
Storage Temperature Range		T_{stg}	-55~150	℃

ELECTRICAL CHARACTERISTICS(Ta=25℃)

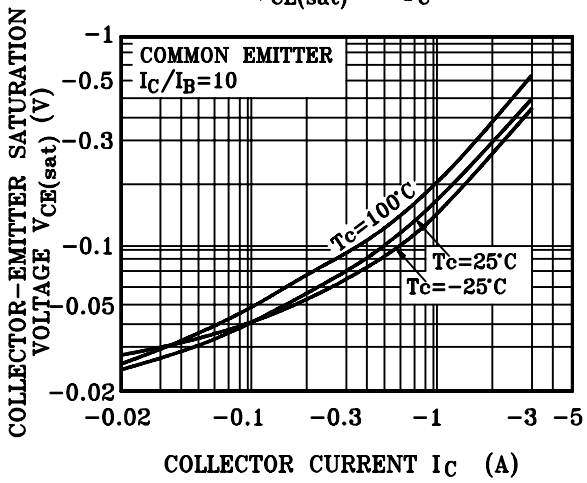
CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current		I_{CBO}	V_{CB}=-60V, I_E=0	-	-	-100	μA
Emitter Cut-off Current		I_{EBO}	V_{EB}=-7V, I_C=0	-	-	-100	μA
Collector-Emitter Breakdown Voltage		$V_{(BR)CEO}$	I_C=-50mA, I_B=0	-60	-	-	V
DC Current Gain		h_{FE}(1) (Note)	V_{CE}=-5V, I_C=-0.5A	60	-	200	
		h_{FE}(2)	V_{CE}=-5V, I_C=-3A	20	-	-	
Collector Emitter Saturation Voltage		$V_{CE(sat)}$	I_C=-2A, I_B=-0.2A	-	-0.25	-1.0	V
Base-Emitter Voltage		V_{BE}	V_{CE}=-5V, I_C=-0.5A	-	-0.7	-1.0	V
Transition Frequency		f_T	V_{CE}=-5V, I_C=-0.5A	-	9	-	MHz
Collector Output Capacitance		C_{ob}	V_{CB}=-10V, I_E=0, f=1MHz	-	150	-	pF
Switching Time	Turn-on Time	t_{on}		-	0.4	-	μS
	Storage Time	t_{stg}		-	1.7	-	
	Fall Time	t_f		-	0.5	-	

Note : h_{FE}(1) Classification O:60~120, Y:100~200

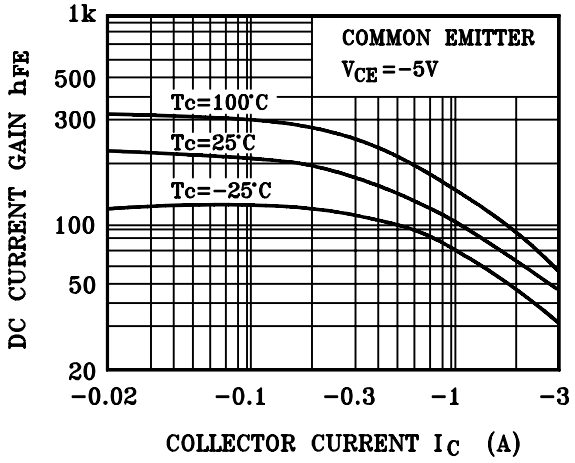
I_C – V_{CE}



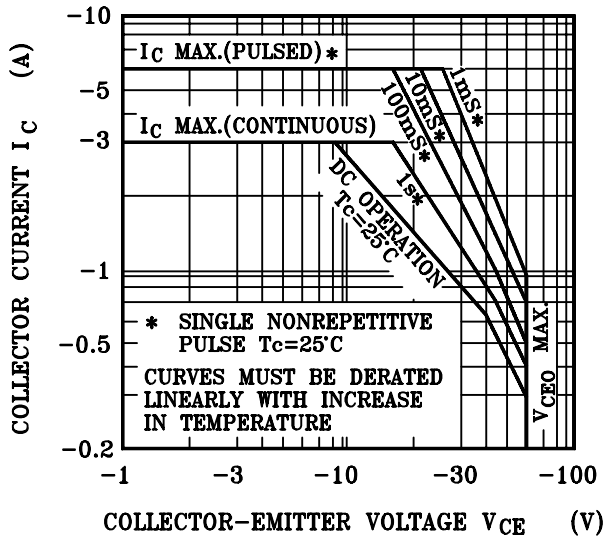
$V_{CE(sat)}$ – I_C



h_{FE} – I_C



SAFE OPERATING AREA



$R_{th(t)}$ – t